

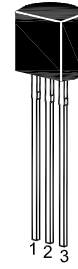
2SD734

NPN Silicon Epitaxial Planar Transistor

for 1W Output, Electronic Governor, DC-DC Converter Applications.

The transistor is subdivided into four groups D, E, F and G, according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



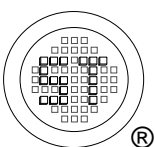
1. Emitter 2. Collector 3. Base
TO-92 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	25	V
Collector Emitter Voltage	V_{CEO}	20	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current	I_C	700	mA
Collector Current (Pulse)	I_{CP}	1500	mA
Power Dissipation	P_{tot}	600	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit	
DC Current Gain at $V_{CE} = 2\text{ V}$, $I_C = 50\text{ mA}$ at $V_{CE} = 2\text{ V}$, $I_C = 500\text{ mA}$	Current Gain Group D	h_{FE}	60	-	120	-
	E	h_{FE}	100	-	200	-
	F	h_{FE}	160	-	320	-
	G	h_{FE}	280	-	560	-
		h_{FE}	50	-	-	-
Collector Base Cutoff Current at $V_{CB} = 20\text{ V}$	I_{CBO}	-	-	1	μA	
Emitter Base Cutoff Current at $V_{EB} = 4\text{ V}$	I_{EBO}	-	-	1	μA	
Gain Bandwidth Product at $V_{CE} = 10\text{ V}$, $I_C = 50\text{ mA}$	f_T	-	250	-	MHz	
Output Capacitance at $V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{ob}	-	8	-	pF	



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ISO 9001 : 2008
Certificate No. 18073308



ISO 14001 : 2004
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